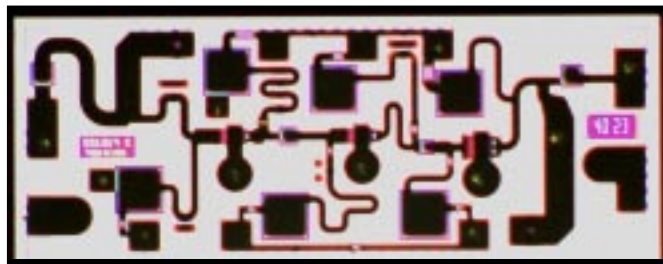


## Ka Band Wideband LNA/Driver

## TGA1319C-EPU



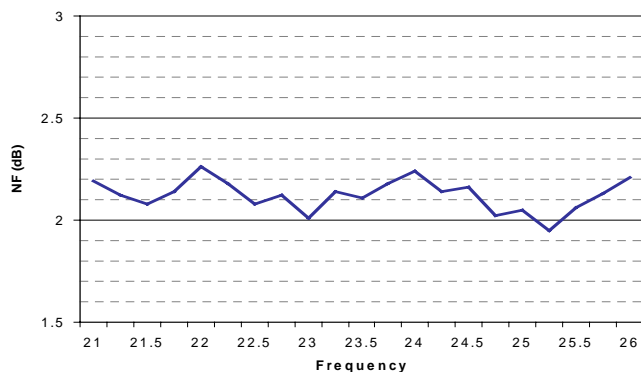
Chip Dimensions 2.179 mm x .847 mm

### Key Features and Performance

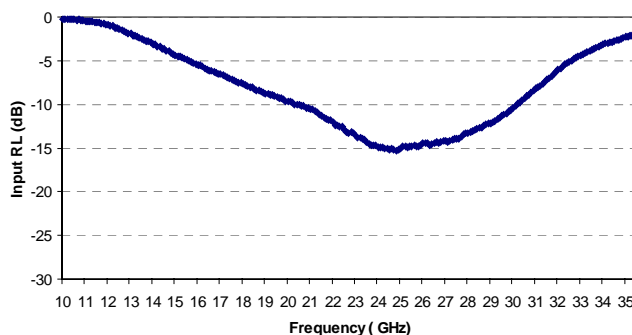
- 0.15um pHEMT Technology
- 16-30 GHz Frequency Range
- 2.25 dB Nominal Noise Figure midband
- 21 dB Nominal Gain
- 14 dBm Pout
- Bias 5V, 60 mA with  $-0.5V < V_g < +0.5V$

### Primary Applications

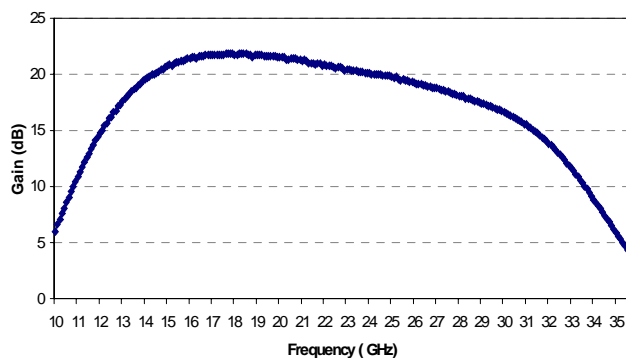
- Point-to-Point Radio
- Point-to-Multipoint Communications



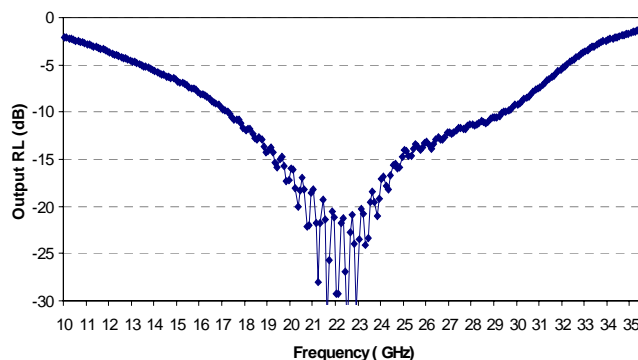
Typical NF @ 25C



Typical S11 @ 25C



Typical Gain @ 25C



Typical S22 @ 25C

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications subject to change without notice*

**MAXIMUM RATINGS**

SYMBOL	PARAMETER <sup>4/</sup>	VALUE	NOTES
V <sup>+</sup>	POSITIVE SUPPLY VOLTAGE	9 V	
I <sup>+</sup>	POSITIVE SUPPLY CURRENT	80 mA	<u>1/</u>
I <sup>-</sup>	NEGATIVE GATE CURRENT	5.28 mA	
P <sub>IN</sub>	INPUT CONTINUOUS WAVE POWER	18 dBm	
P <sub>D</sub>	POWER DISSIPATION	.72 W	
T <sub>CH</sub>	OPERATING CHANNEL TEMPERATURE	150 °C	<u>2/</u> <u>3/</u>
T <sub>M</sub>	MOUNTING TEMPERATURE (30 SECONDS)	320 °C	
T <sub>STG</sub>	STORAGE TEMPERATURE	-65 to 150 °C	

1/ Total current for all stages.

2/ These ratings apply to each individual FET.

3/ Junction operating temperature will directly affect the device median time to failure (T<sub>M</sub>). For maximum life, it is recommended that junction temperatures be maintained at the lowest possible levels.

4/ These ratings represent the maximum operable values for the device.

**DC PROBE TESTS**

(T<sub>A</sub> = 25 °C ± 5°C)

Symbol	Parameter	Minimum	Maximum	Value
I <sub>DSS</sub>	Saturated Drain Current	---	---	mA
V <sub>P</sub>	Pinch-off Voltage	-1.5	-0.5	V
BVGS	Breakdown Voltage gate-source	---	---	V
BVGD	Breakdown Voltage gate-drain	---	---	V

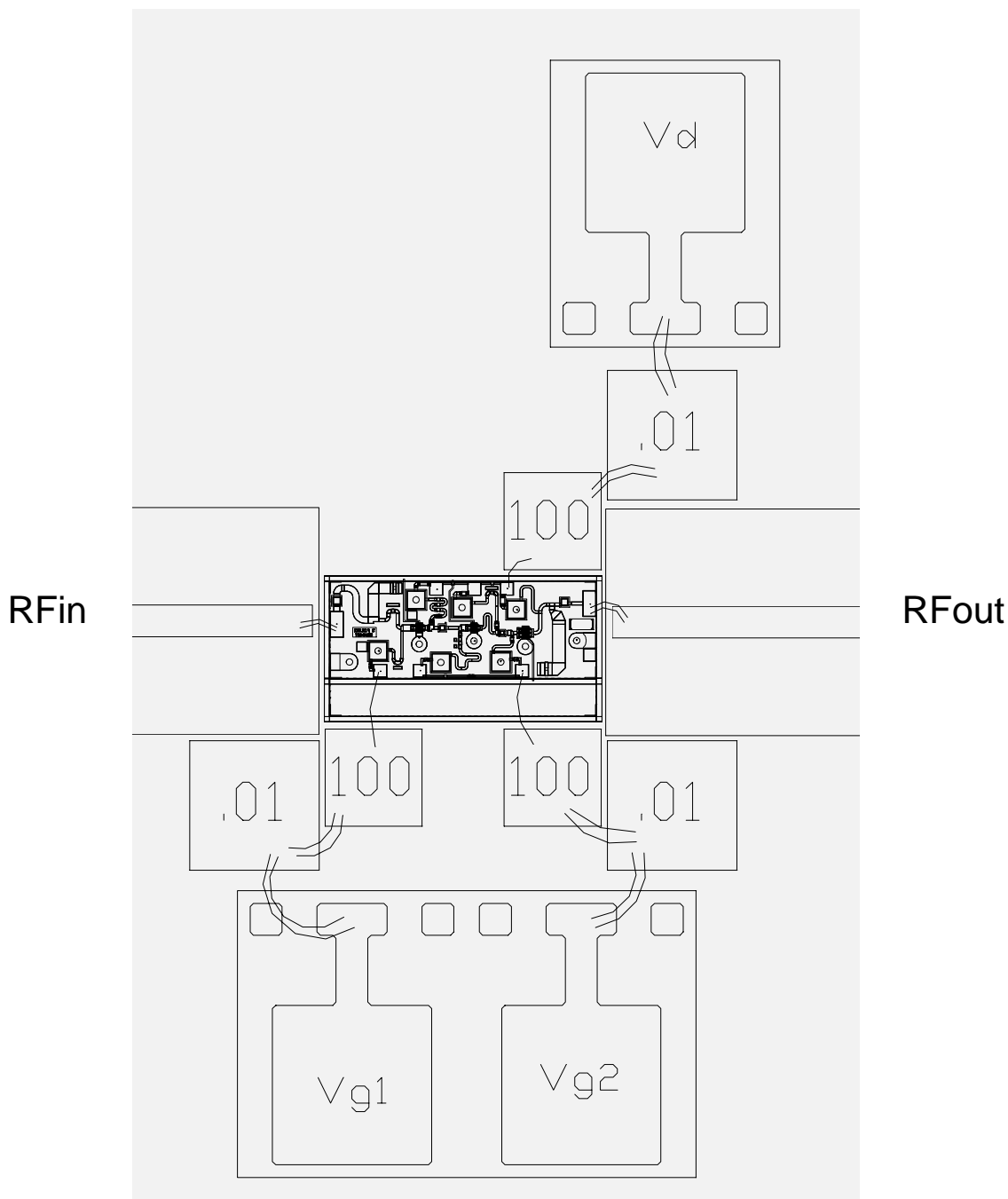
**ON-WAFER RF PROBE CHARACTERISTICS**

(T<sub>A</sub> = 25 °C ± 5°C)

V<sub>d</sub> = 5 V, I<sub>d1</sub> = 10 mA, I<sub>d2</sub> = 50 mA

Symbol	Parameter	Test Condition	Limit			Units
			Min	Typ	Max	
Gain	Small Signal Gain	F = 21 – 27 GHz	19		---	dB
NF	Noise Figure	F = 21 – 25 GHz	---		2.5	dB
		F = 26 – 26.5 GHz	---		2	
PWR	Output Power @ P1dB	F = 21 – 26 GHz	10		---	dBm
		F = 27 GHz	9		---	

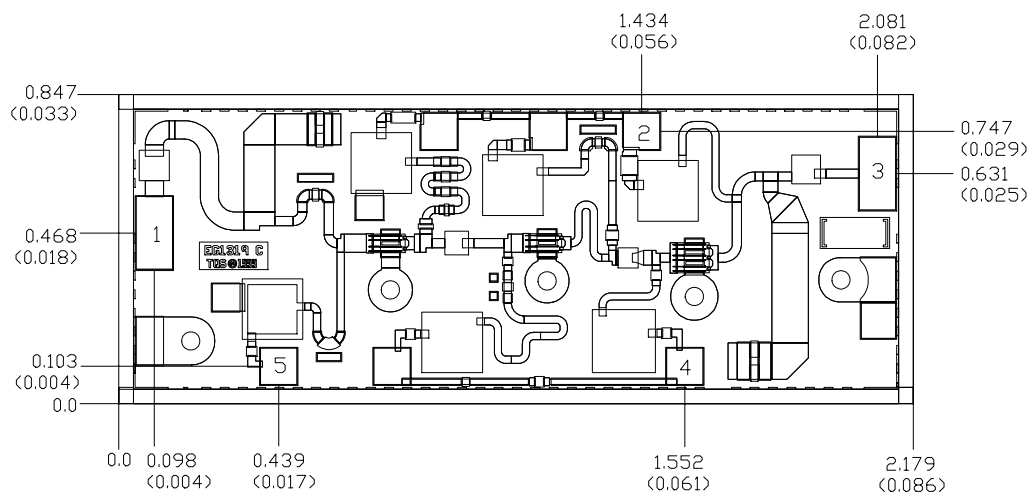
*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications subject to change without notice*



- Notes: 1. Vg1 and Vg2 may be sourced from the same supply.  
 2. Positive or negative gate bias may be required to achieve recommended operating point.

**TGA1319C- Recommended Assembly Drawing**

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications subject to change without notice*



Units: millimeters (inches)

Thickness: 0.1016 (0.004)

Chip edge to bond pad dimensions are shown to center of bond pad

Chip size tolerance: +/- 0.051 (0.002)

Bond Pad #1 (RF Input)	0.100 x 0.200 (0.004 x 0.008)
Bond Pad #2 (Vd)	0.100 x 0.100 (0.004 x 0.004)
Bond Pad #3 (RF Output)	0.100 x 0.200 (0.004 x 0.008)
Bond Pad #4 (Vg2)	0.100 x 0.100 (0.004 x 0.004)
Bond Pad #5 (Vg1)	0.100 x 0.100 (0.004 x 0.004)

### Mechanical Drawing

*Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications subject to change without notice*

## Assembly Process Notes

### Reflow process assembly notes:

- Use AuSn (80/20) solder with limited exposure to temperatures at or above 300°C.
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- No fluxes should be utilized.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

### Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.
- Microwave or radiant curing should not be used because of differential heating.
- Coefficient of thermal expansion matching is critical.

### Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonics are critical parameters.
- Aluminum wire should not be used.
- Discrete FET devices with small pad sizes should be bonded with 0.0007-inch wire.
- Maximum stage temperature is 200°C.

***GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.***

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